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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No.: 035532-0141

International re patent application of

Yuichi OSHIMA et al.

Serial No.: 10/821,921

Group Art Unit: 2813

Filed: April 12, 2004

Examiner: David S. Blum

For: POROUS SUBSTRATE FOR EPITAXIAL GROWTH, METHOD FOR
MANUFACTURING SAME, AND METHOD FOR MANUFACTURING III-
NITRIDE SEMICONDUCTOR SUBSTRATE

**RESPONSE TO RESTRICTION REQUIREMENT
AND ELECTION OF SPECIES REQUIREMENT**

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated January 31, 2006, Applicants hereby elect the claims of Group I, claims 1-13, for prosecution in the subject application.

Further, in reply to the Election of Species Requirements, Applicants hereby elect the Species such that "Base Material" is Sapphire; "The Porous Substrate" is III-nitride on a base material; "III-Nitride semiconductor is prepared from" GaN; and "The porous metallic layer is prepared from" Nitrides of Titanium. Claims 1, 3-14, 16-25 and 27-35 are readable on the elected species. The examiner indicates that no claim is generic. However, Applicants believe claim 1 is generic.

Applicant, of course, reserves the right to file a divisional application(s) covering the subject matter of the non-elected claims.

Receipt of the initial Office Action on the merits is awaited.

Respectfully submitted,

By 

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Date: February 28, 2006

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